4Mb (256K x 16) Pseudo Static RAM

Features

- Wide voltage range: **2.70V–3.30V**
- Access Time: 70ns
- Ultra-low active power
  - **— Typical active current: 2.0mA @ f = 1 MHz**
  - **— Typical active current: 13mA @ f = f_{max}**
- Ultra low standby power
- Automatic power-down when deselected
- CMOS for optimum speed/power
- Offered in a 48 Ball BGA Package

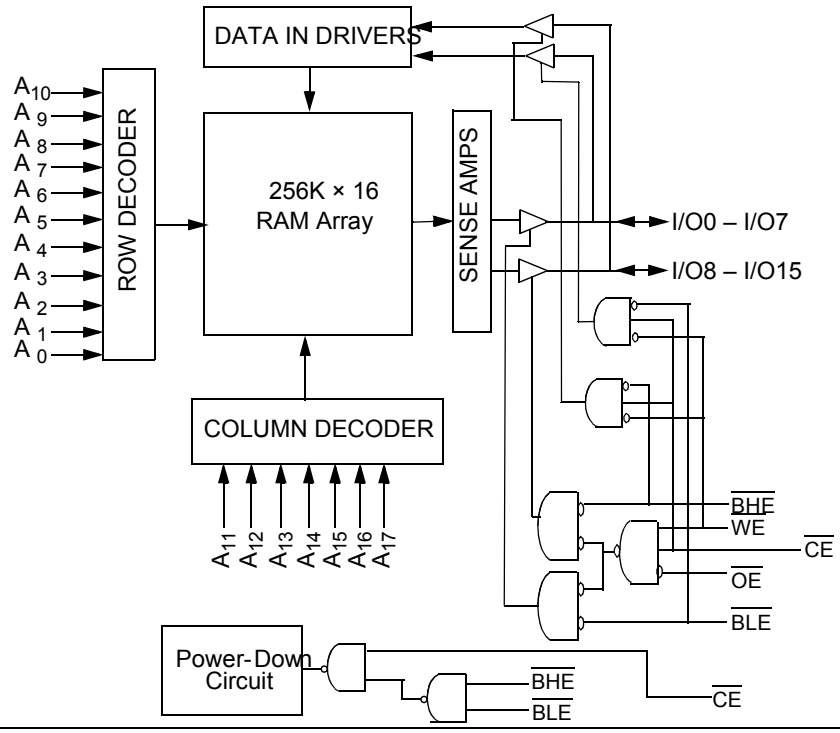
Functional Description[1]

The CG6257AM is a high-performance CMOS Pseudo static RAM organized as 256K words by 16 bits that supports an asynchronous memory interface. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life® (MoBL) in portable applications such as cellular telephones. The device can be put into standby mode reducing power consumption by more than 99% The device can also be put into standby mode when deselected ($\overline{CE}$ HIGH or both $\overline{BHE}$ and $\overline{BLE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW). **The addresses must not be toggled once the read is started on the device.**

Writing to the device is accomplished by taking Chip Enables ($\overline{CE}$ LOW) and Write Enable ($\overline{WE}$) input LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enables ($\overline{CE}$ LOW) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this datasheet for a complete description of read and write modes

Logic Block Diagram



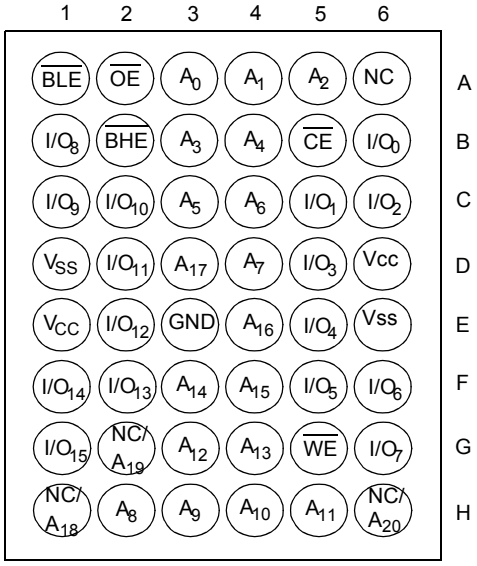
Note:

1. For best-practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration[2, 3, 4]

FBGA

Top View



Note:

2. DNU pins have to be left floating.
3. Ball H1, G2 and ball H6 for the FBGA package can be used to upgrade to a 8M, 16M and a 32M density respectively.
4. NC “no connect” - not connected internally to the die.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to + 150°C

Ambient Temperature with Power Applied.....–55°C to + 125°C

Supply Voltage to Ground Potential..... –0.4V to 4.6V

DC Voltage Applied to Outputs in High Z State[5, 6, 7] .....–0.4V to 3.3V

DC Input Voltage[5, 6, 7].....–0.4V to 3.3V

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current .....>200 mA

Operating Range[9]

Device	Range	Ambient Temperature	V_{CC}
CG6257AM	Industrial	–25°C to +85°C	2.70V to 3.30V

Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC}(mA)				Standby I_{SB2}(µA)	
					f = 1MHz		f = f_{max}			
	Min.	Typ.[8]	Max.		Typ.[8]	Max.	Typ.[8]	Max.	Typ.[8]	Max.
CG6257AM	2.70	3.0	3.30	70	2	4	13	17	55	80

Notes:

5. $V_{IL(MIN)}$ = -0.5V for pulse durations less than 20ns.
6. $V_{IH(Max)}$ = Vcc + 0.5V for pulse durations less than 20ns.
7. Overshoot and undershoot specifications are characterized and are not 100% tested.
8. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ.)}$, T_A = 25°C.
9. Vcc must be at minimal operational levels before inputs are turned ON.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CG6257AM-70 Min.	Typ.[8]	Max.	Unit
V_{CC}	Supplay Voltage			2.7		3.3	V
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 2.70V	2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.0mA	V_{CC} = 2.70V			0.4	V
V_{IH}	Input HIGH Voltage	V_{CC}= 2.7V to 3.3V		0.8*Vcc		V_{CC} +0.3V	V
V_{IL}	Input LOW Voltage	V_{CC}= 2.7V to 3.3V(F = 0)		-0.3		0.4	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	V_{CC} = V_{CCmax} I_{OUT} = 0 mA CMOS levels		13	17	mA
		f = 1 MHz			2.0	4	mA
I_{SB1}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC}–0.2V V_{IN}≥V_{CC}–0.2V, V_{IN}≤0.2V) f = f_{MAX} (Address and Data Only), f = 0 (OE, WE, BHE and BLE), V_{CC}=3.30V	Vcc = 3.3V			350	µA
I_{SB2}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.30V	Vcc = 3.3V		55	80	µA

Capacitance[10]

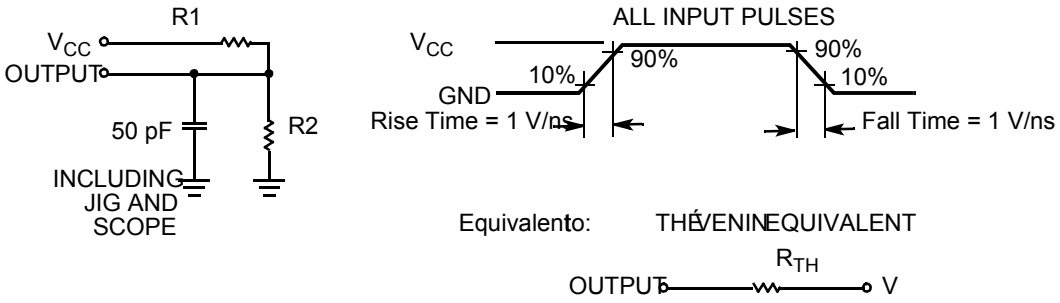
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	6	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[10]

Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	Θ_{JA}	55	°C/W
Thermal Resistance (Junction to Case)		Θ_{JC}	16	°C/W

Note:
10. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Parameters	3.0V V_{CC}	Unit
R1	1179	Ω
R2	1941	Ω
R_{TH}	733	Ω
V_{TH}	1.87	V

Switching Characteristics Over the Operating Range[11]

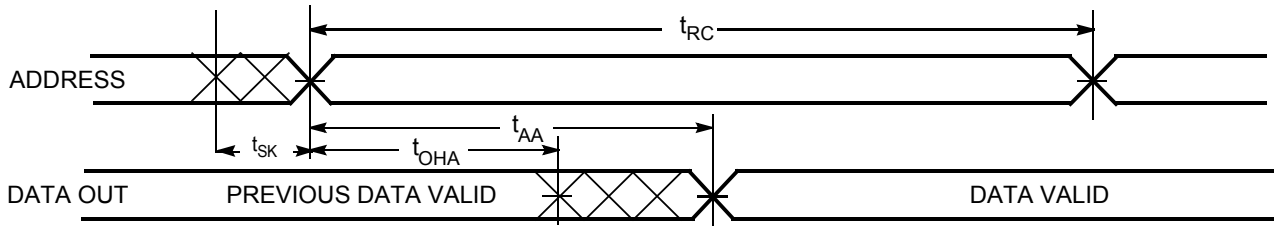
Parameter	Description	70 ns		Unit
		Min.	Max.	
READ CYCLE				
t_{RC}	Read Cycle Time	70		ns
t_{AA}	Address to Data Valid		70	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		35	ns
t_{LZOE}	$\overline{OE}$ LOW to LOW Z[12, 14]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[12, 14]		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[12, 14]	5		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[12, 14]		25	ns
t_{DBE}	BLE / BHE LOW to Data Valid		70	ns
t_{LZBE}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Low Z[12, 14]	5		ns
t_{HZBE}	$\overline{BLE}$ / $\overline{BHE}$ HIGH to HIGH Z[12, 14]		25	ns
t_{SK}	**Address Skew**		**0**	**ns**
WRITE CYCLE[13]				
t_{WC}	Write Cycle Time	70		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	60		ns
t_{AW}	Address Set-Up to Write End	60		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	45		ns
t_{BW}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Write End	60		ns
t_{SD}	Data Set-Up to Write End	45		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[12, 14]		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[12, 14]	5		ns

Notes:

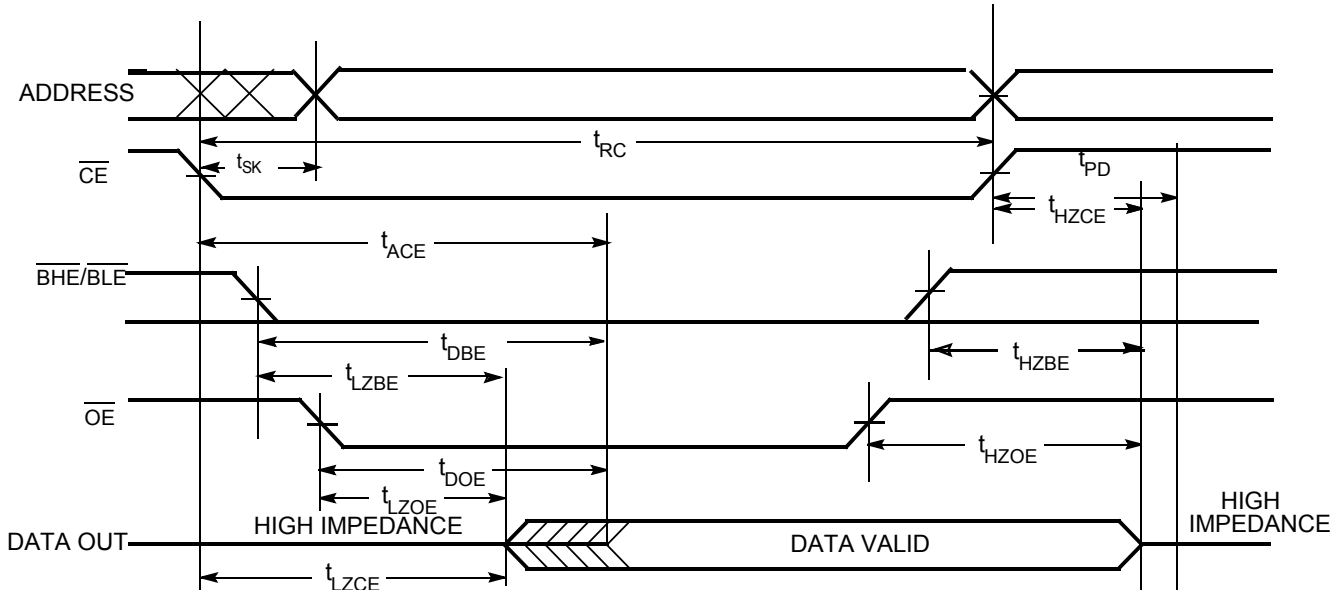
11. Test conditions for all parameters other than tri-state parameters assume signal transition time of 1ns/V, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0V to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section..
12. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedence state.
13. The internal Write time of the memory is defined by the overlap of WE, CE = V_{IL}, BHE and/or BLE = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write
14. High-Z and Low-Z parameters are characterized and are not 100% tested. .

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)[15, 16]



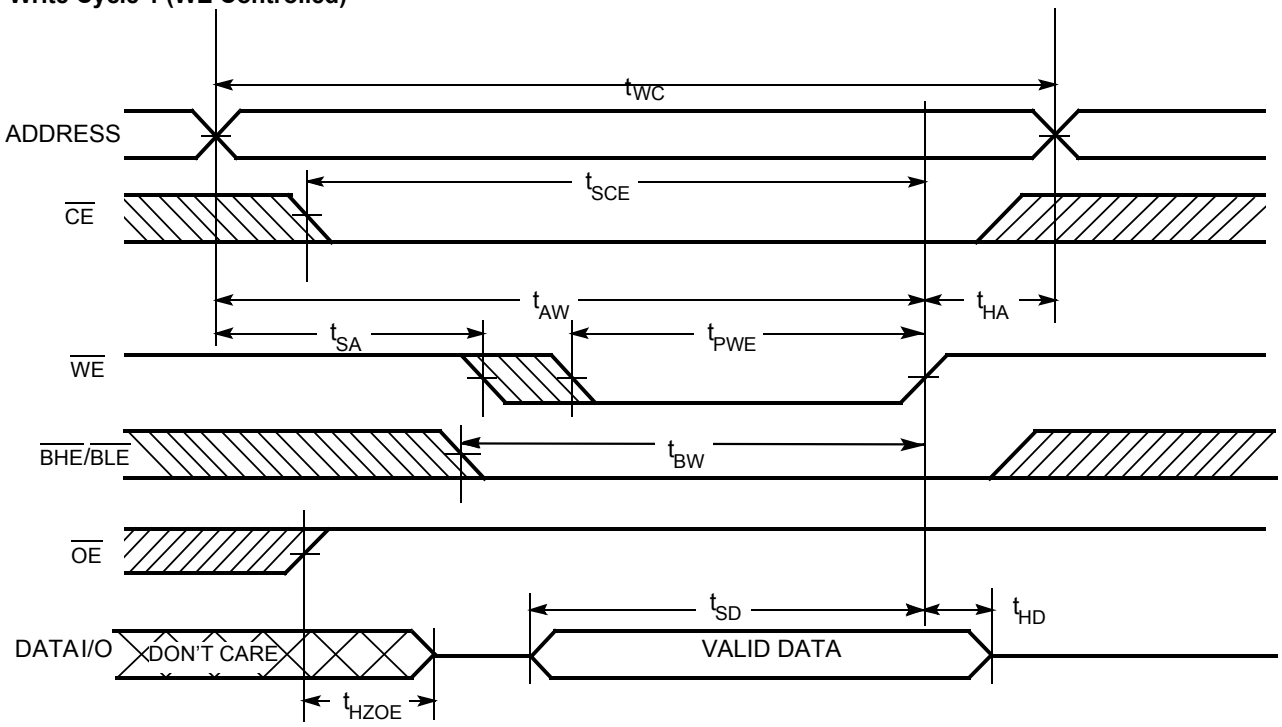
Read Cycle 2 ($\overline{OE}$ Controlled)[15, 16]



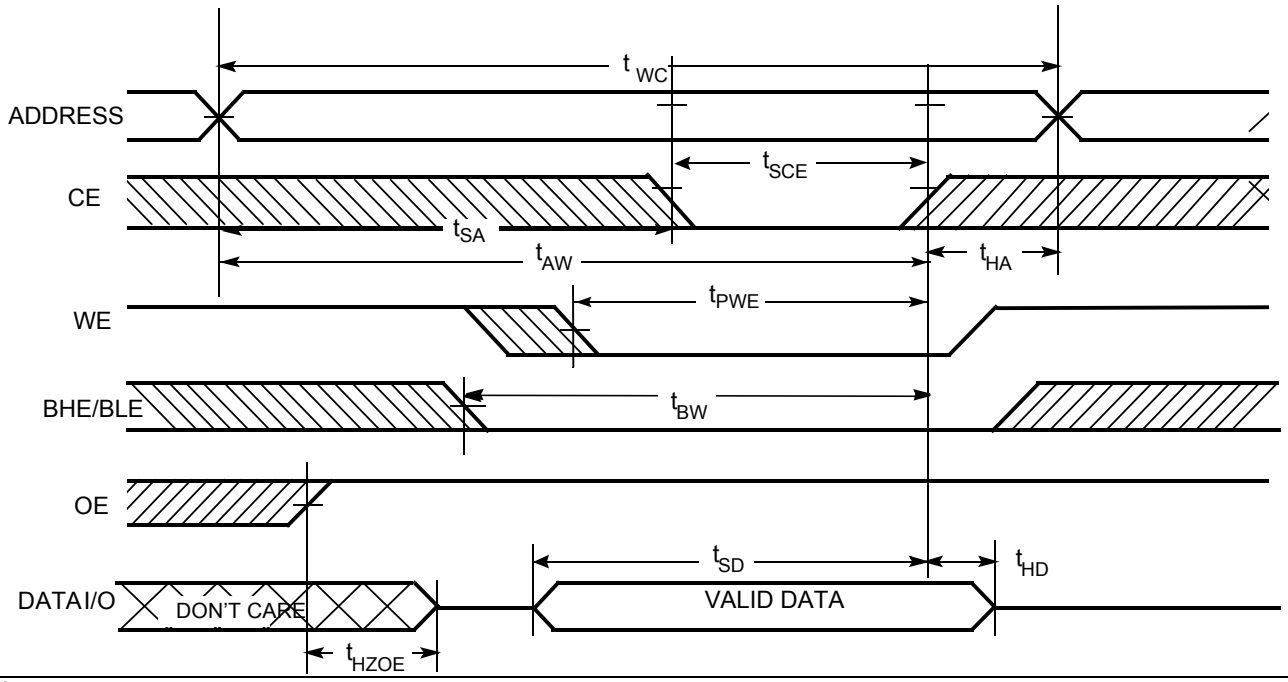
Note:
15. $\overline{WE}$ is HIGH for Read Cycle.
16. **Addresses should not be toggled after the start of a read cycle**

Switching Waveforms (continued)

Write Cycle 1 ($\overline{WE}$ Controlled) [13, 14, 17, 18, 19]



Write Cycle 2 ($\overline{CE}$ Controlled) [13, 14, 17, 18, 19]

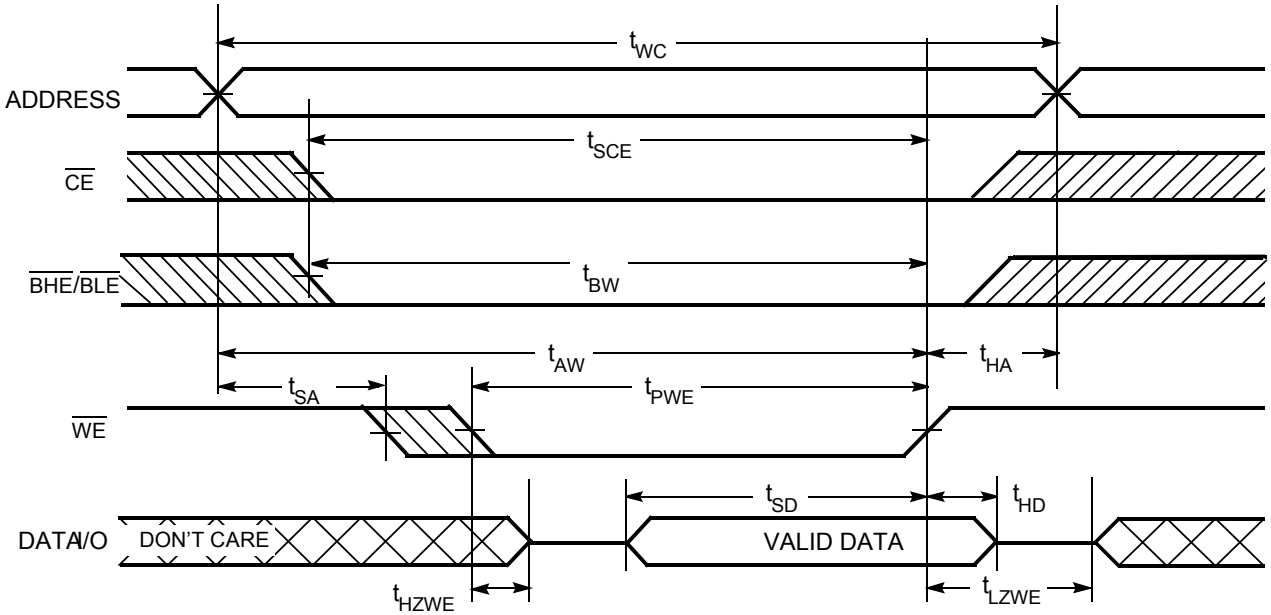


Notes:

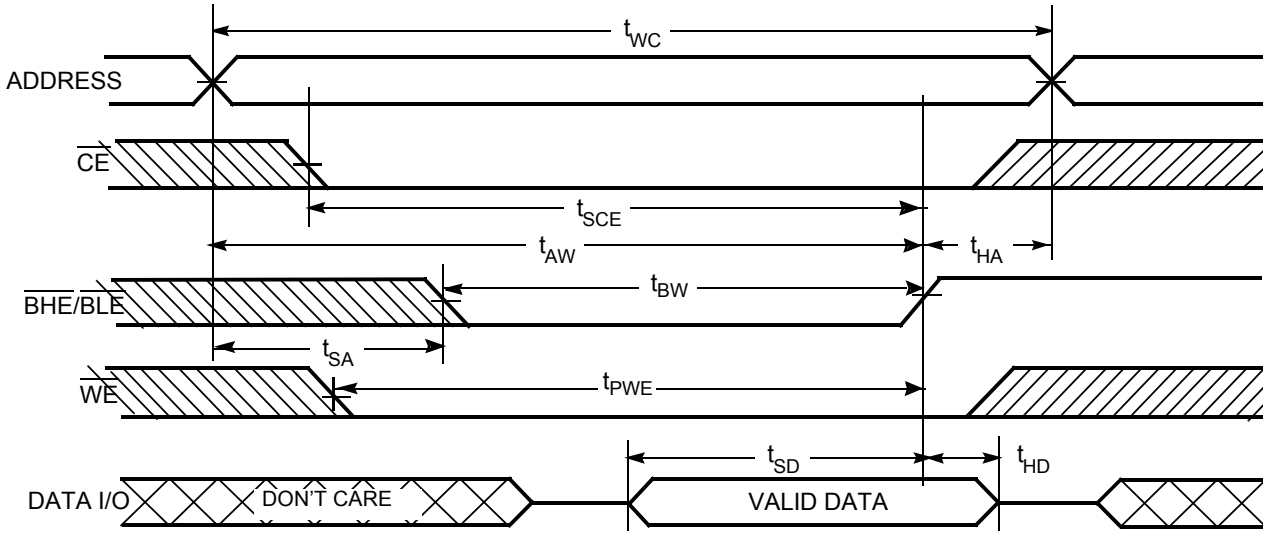
17. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
18. If Chip Enable goes INACTIVE with $\overline{WE}$ = V_{IH}, the output remains in a high-impedance state.
19. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[18, 19]



Write Cycle 4 ($\overline{BHE}$/$\overline{BLE}$ Controlled, $\overline{OE}$ LOW)[18, 19]



Truth Table[20]

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
X	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O0 – I/O15)	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O0 – I/O7); High Z (I/O8 – I/O15)	Read	Active (I_{CC})
L	H	L	L	H	High Z (I/O0 – I/O7); Data Out (I/O8 – I/O15)	Read	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O0 – I/O15)	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O0 – I/O7); High Z (I/O8 – I/O15)	Write	Active (I_{CC})
L	L	X	L	H	High Z (I/O0 – I/O7); Data In (I/O8 – I/O15)	Write	Active (I_{CC})

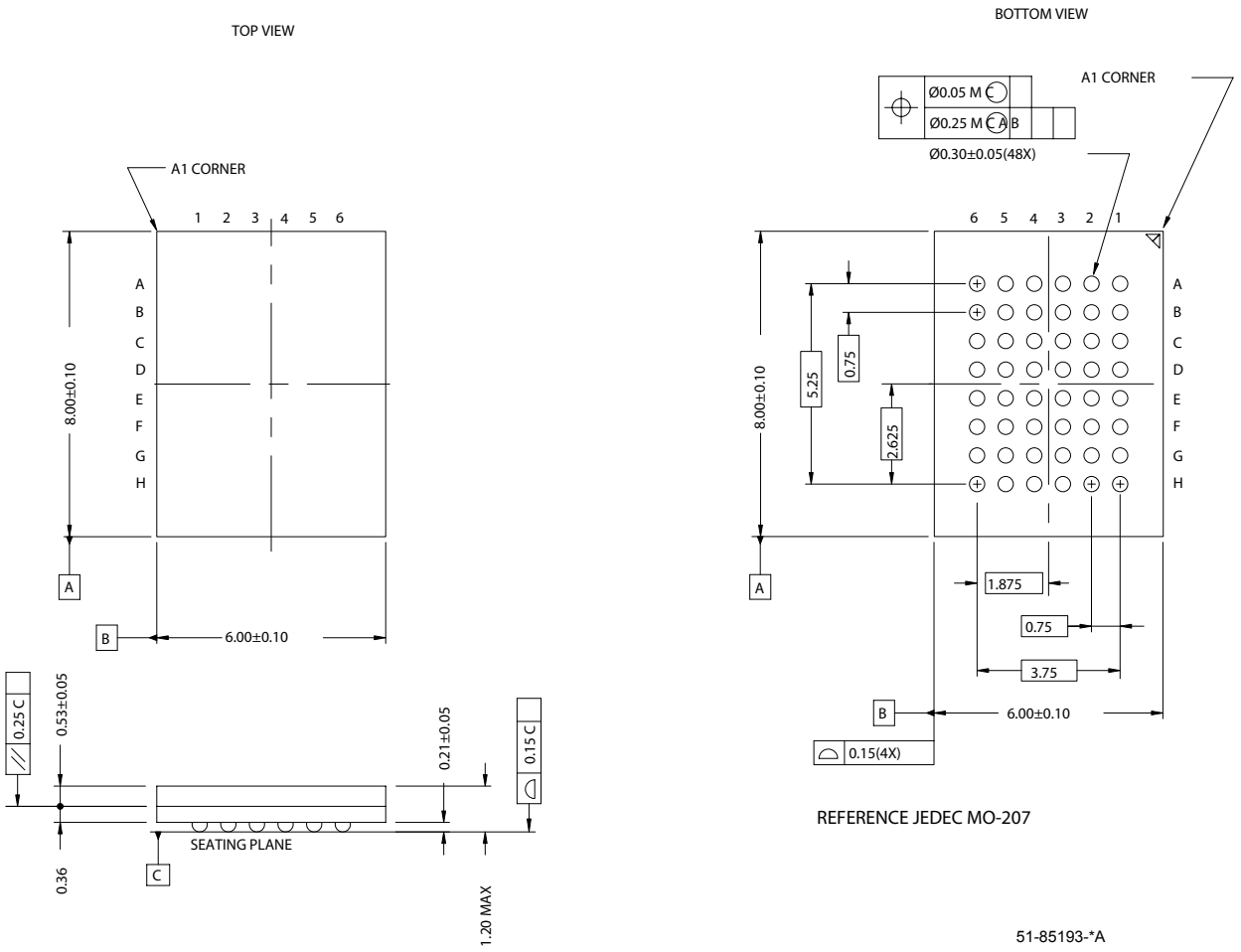
Note:
20. H = V_{IH}, L = V_{IL}, X = Don't Care

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CG6257AM	BA48K	48-ball Fine Pitch BGA (6 mm × 8mm × 1.2 mm)	Industrial

Package

48-Ball (6 mm x 8mm x 1.2 mm) FBGA BA48K



Document Title: CG6257AM MoBL3® 4Mb (256K x 16) Pseudo Static RAM Document Number: 38-XXXXX				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**		10/21/03	MPR	New Datasheet